

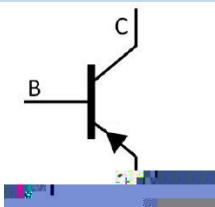
SOT-23

PNP

Silicon PNP transistor in a SOT-23 Plastic Package.

Low current ,Low voltage ,S-mini package, HF Product.

General power amplifier application.



PIN1

Base

PIN 2

Emitter

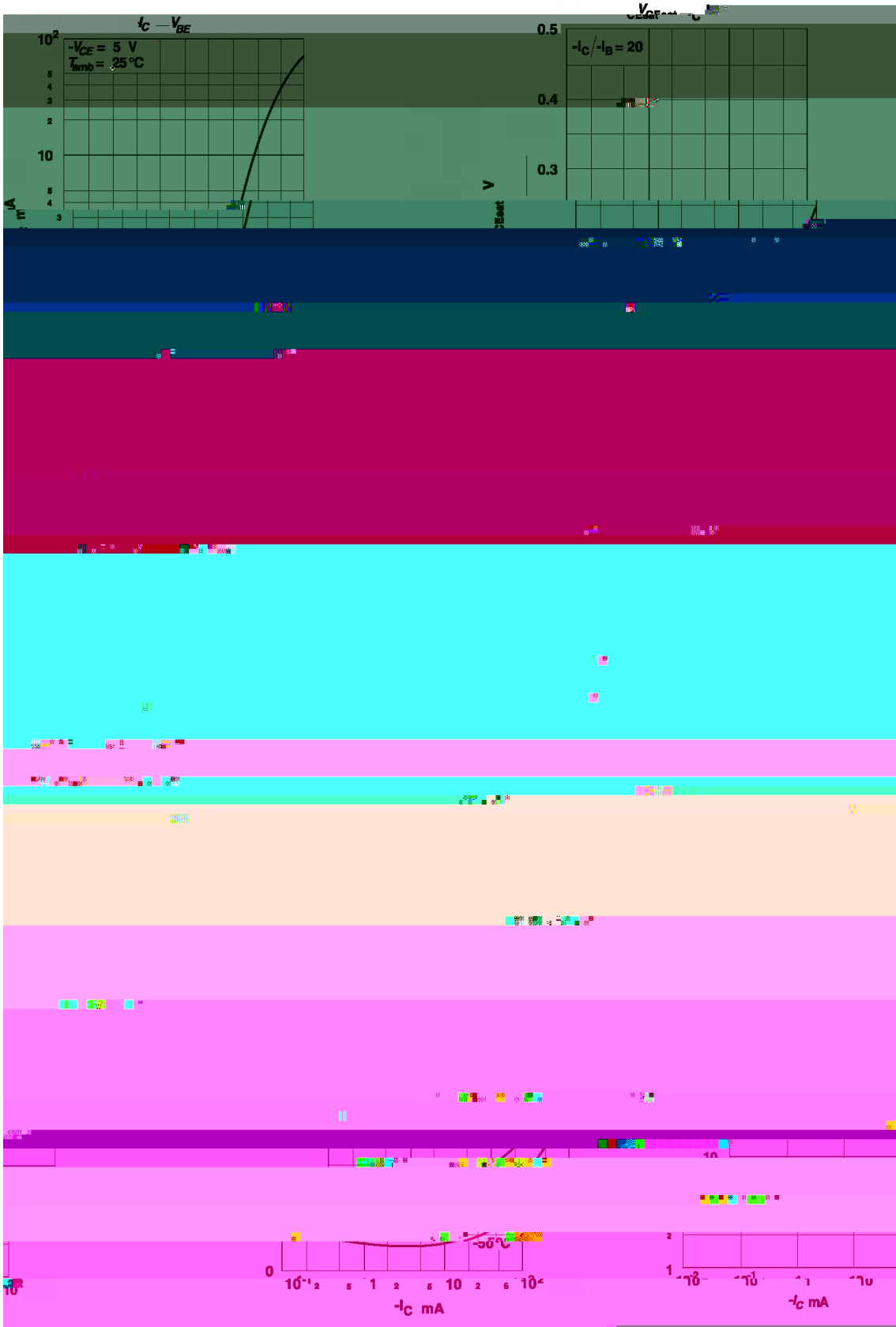
PIN 3

Collector

h _{FE} Classifications Symbol	A	B
h _{FE} Range	125 250	220 475
Marking	G3A	G3B

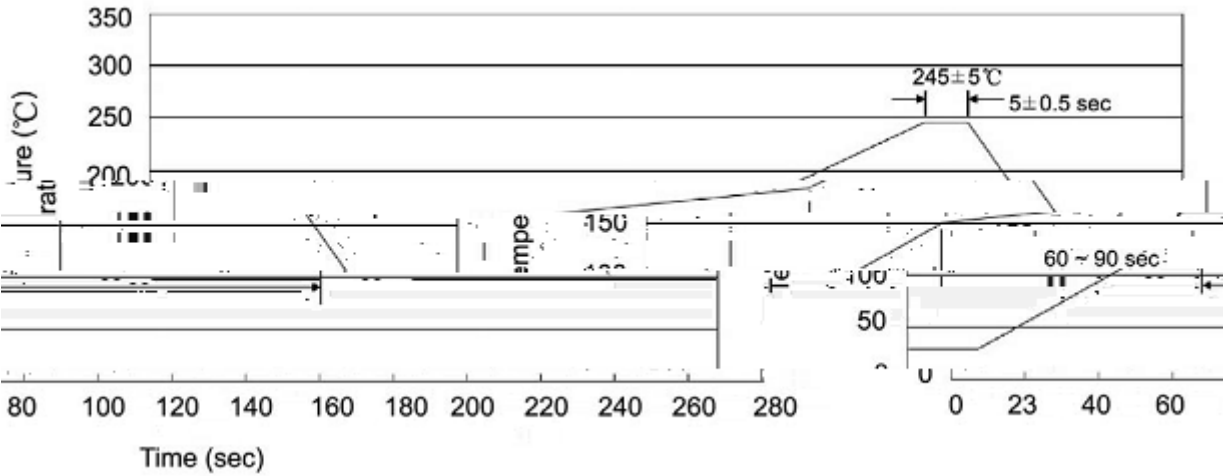
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-65	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-100	mA
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-30V$ $I_E=0$			-0.015	μA
DC Current Gain	h_{FE}	$V_{CE}=-5.0V$ $I_C=-2.0mA$	125		475	
Collector-Emitter Saturation Voltage	$V_{CE(sat) (1)}$	$I_C=-10mA$ $I_B=-0.5mA$		-0.09	-0.3	V
	$V_{CE(sat) (2)}$	$I_C=-100mA$ $I_B=-5.0mA$		-0.25	-0.65	V
Base-Emitter Saturation Voltage	$V_{BE(sat) (1)}$	$I_C=-10mA$ $I_B=-0.5mA$		-0.7		V
	$V_{BE(sat) (2)}$	$I_C=-100mA$ $I_B=-5.0mA$		-0.9		V
Base-Emitter Voltage	$V_{BE(ON)1}$	$V_{CE}=-5.0V$ $I_C=-2.0mA$	-0.6	-0.65	-0.75	V
	$V_{BE(ON)2}$	$V_{CE}=-5.0V$ $I_C=-10mA$			-0.82	V
Transition Frequency	f_T	$V_{CE}=-5.0V$ $I_E=10mA$ $f=100MHz$		150		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V$ $I_E=0$ $f=1MHz$		4.5		pF
Noise Figure	NF	$V_{CE}=-6.0V$ $I_C=-0.2mA$ $R_g=2K\Omega$ $f=1KHz$		2.0	10	dB





Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- 1

25 150

60 90sec;

2

245±5

5±0.5sec;

3

2 10 /sec.
- 1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:245±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

260±5

10±1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
SOT-23	3,000	10	30,000	8	180,000	7 ×8	180×120×180	390×385×205